



## Features

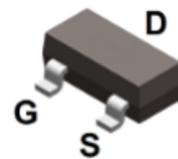
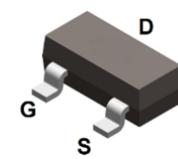
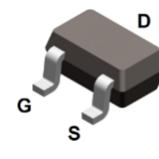
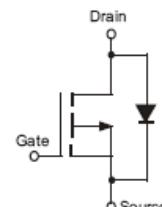
- Advanced trench technology
- High-speed switching
- Drive circuits can be simple
- Parallel use is easy

## Typical Applications

- P-channel enhancement mode effect transistor
- Switching application

## Mechanical Data

- Case: SOT-23, SOT-23-3L, SOT-323
- Molding Compound: UL Flammability Classification Rating 94V-0
- Terminals: Matte tin-plated leads; solderability-per MIL-STD-202, Method 208

BSS84  
SOT-23BSS84-3L  
SOT-23-3LBSS84W  
SOT-323

## Ordering Information

Part Number	Package	Shipping Quantity	Marking Code
BSS84	SOT-23	3000 pcs / Tape & Reel	SP
BSS84-3L	SOT-23-3L	3000 pcs / Tape & Reel	SP
BSS84W	SOT-323	3000 pcs / Tape & Reel	K84

## Maximum Ratings (@ $T_A = 25^\circ\text{C}$ unless otherwise specified)

Parameter	Symbol	Value	Unit
Drain-to-Source Voltage	$V_{DSS}$	-50	V
Gate-to-Source Voltage	$V_{GSS}$	$\pm 12$	V
Continuous Drain Current ( $T_A = 25^\circ\text{C}$ ) <sup>*1</sup>	$I_D$	-130	mA
Pulsed Drain Current ( $t_p = 10\mu\text{s}$ , $T_A = 25^\circ\text{C}$ )	$I_{DM}$	-520	mA
Single Pulse Avalanche Energy <sup>*3</sup>	$E_{AS}$	0.4	mJ
Power Dissipation ( $T_A = 25^\circ\text{C}$ ) <sup>*1</sup>	$SOT-23$	0.36	W
	$SOT-23-3L$	0.36	
	$SOT-323$	0.2	
Operating Junction Temperature Range	$T_J$	-55 ~ +150	°C
Storage Temperature Range	$T_{STG}$	-55 ~ +150	°C

## Thermal Characteristics

Parameter	Symbol	Value	Unit
Thermal Resistance Junction-to-Air <sup>**</sup>	$R_{\text{JJA}}$	350	°C/W
		625	

**BSS84/BSS84-3L/BSS84W****P-Channel Enhancement Mode MOSFET****Electrical Characteristics** (@  $T_A = 25^\circ\text{C}$  unless otherwise specified)

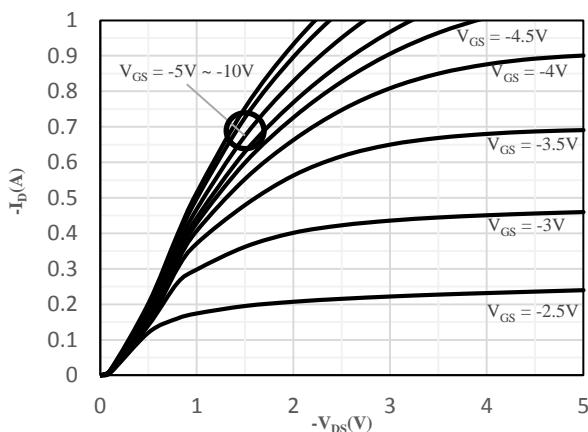
Symbol	Parameter	Test Condition	Min.	Typ.	Max.	Unit
<b>Static Characteristics</b>						
$V_{DSS}$	Drain-Source Breakdown Voltage	$V_{GS} = 0V, I_D = -250\mu\text{A}$	-50	-	-	V
$I_{DS(0)}$	Zero Gate Voltage Drain Current	$V_{DS} = -50V, V_{GS} = 0V$	-	-	-1	$\mu\text{A}$
$I_{GSS}$	Gate-Body Leakage Current	$V_{GS} = \pm 20V, V_{DS} = 0V$	-	-	$\pm 10$	$\mu\text{A}$
<b>On Characteristics</b>						
$R_{DS(ON)}$	Drain-Source On-resistance <sup>*2</sup>	$V_{GS} = -5V, I_D = -0.1\text{A}$	-	2.1	10	$\Omega$
$V_{GS(TH)}$	Gate Threshold Voltage	$V_{DS} = V_{GS}, I_D = -1\text{mA}$	-0.8	-1.5	-2	V
$R_G$	Gate Resistance	$V_{GS} = 0V, f = 1\text{MHz}$	-	84	-	$\Omega$
<b>Dynamic Characteristics</b>						
$C_{iss}$	Input Capacitance	$V_{GS} = 0V$	-	48	-	pF
$C_{oss}$	Output Capacitance	$V_{DS} = -20V$	-	15	-	
$C_{rss}$	Reverse Transfer Capacitance	$f = 1.0\text{MHz}$	-	3	-	
<b>Switching Characteristics</b>						
$t_{d(on)}$	Turn-on Delay Time <sup>*4</sup>	$V_{DD} = 30V, I_D = 0.2\text{A}$ $V_{GS} = 10V, R_G = 25\Omega$ $R_L = 150\Omega$	-	6	-	nS
$t_r$	Turn-on Rise Time <sup>*4</sup>		-	5	-	
$t_{d(off)}$	Turn-Off Delay Time <sup>*4</sup>		-	25	-	
$t_f$	Turn-Off Fall Time <sup>*4</sup>		-	15	-	
$Q_G$	Total Gate-Charge	$V_{DD} = -30V$ $V_{GS} = -4.5V$ $I_D = -0.2\text{A}$	-	2.1	-	nC
$Q_{GS}$	Gate to Source Charge		-	0.78	-	
$Q_{GD}$	Gate to Drain (Miller) Charge		-	0.4	-	
<b>Source-Drain Diode Characteristics</b>						
$V_{SD}$	Diode Forward Voltage <sup>*2</sup>	$I_S = -0.26\text{A}, V_{GS} = 0V$	-	-1.15	-1.4	V

Notes:

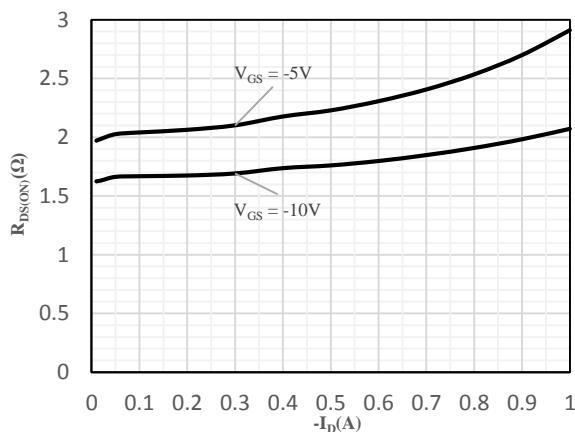
- 1、 Surface mounted on FR4 board, and standard footprint,  $t \leq 10$  sec
- 2、 The data tested by pulsed, pulse width  $\leq 300\mu\text{s}$ , duty cycle  $\leq 2\%$
- 3、 The  $E_{AS}$  data shows Max. rating. The test condition is  $V_{DD} = -30V, V_{GS} = -10V, L = 0.1\text{mH}$
- 4、 Guaranteed by design, not subject to production



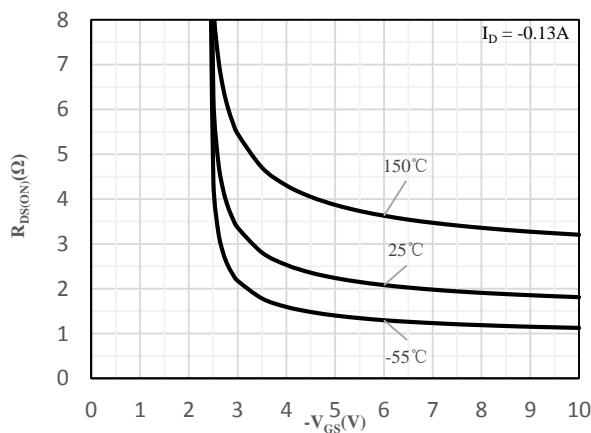
## Ratings and Characteristics Curves (@ $T_A = 25^\circ\text{C}$ unless otherwise specified)



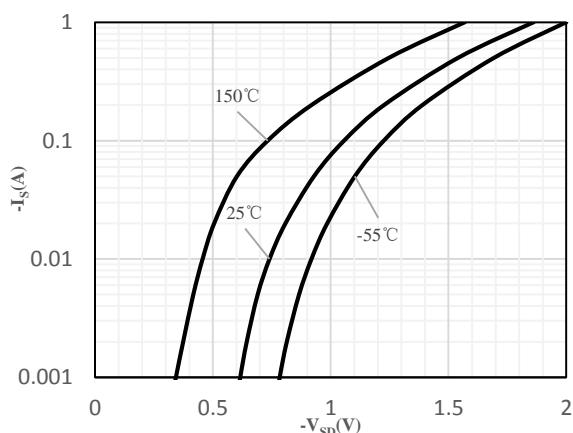
**Fig 1 Typical Output Characteristics**



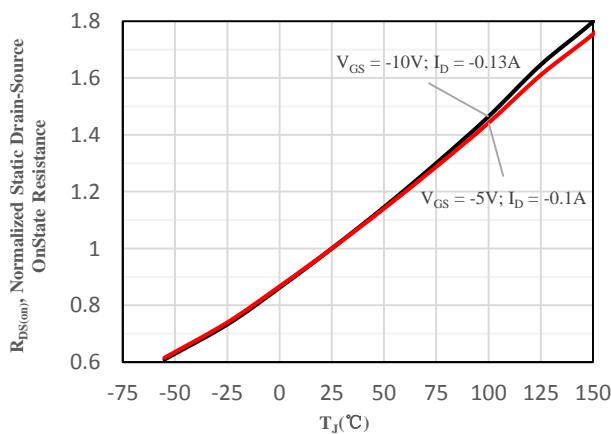
**Fig 2 On-Resistance vs. Drain Current and Gate Voltage**



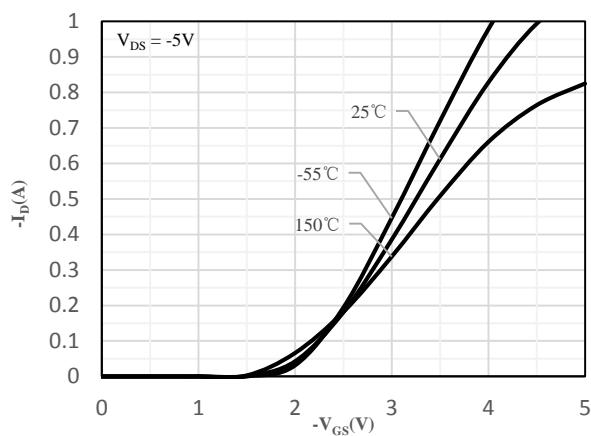
**Fig 3 On-Resistance vs. Gate-Source Voltage**



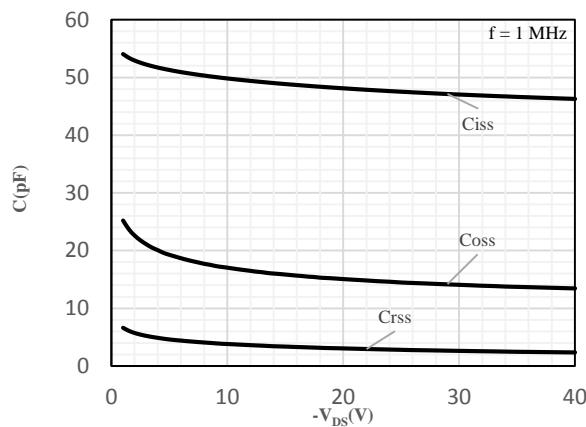
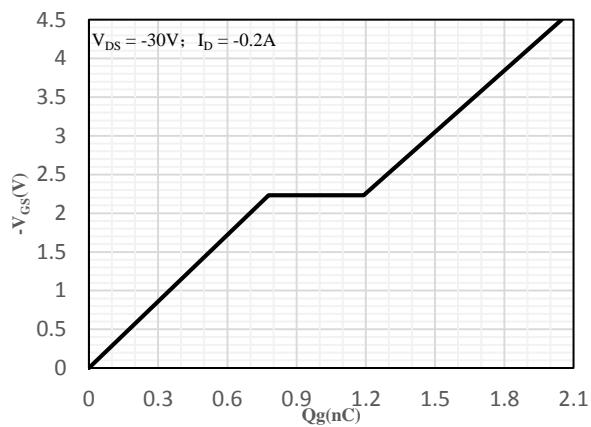
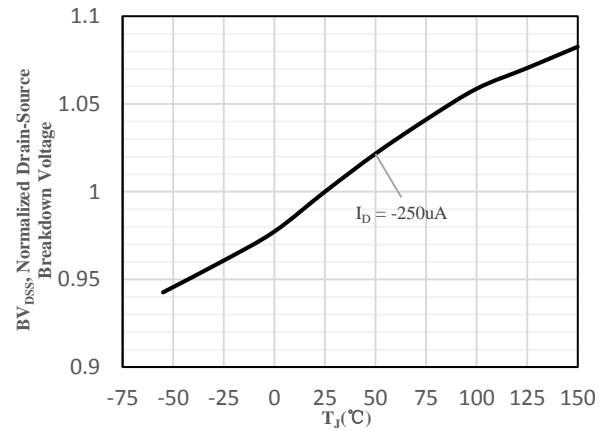
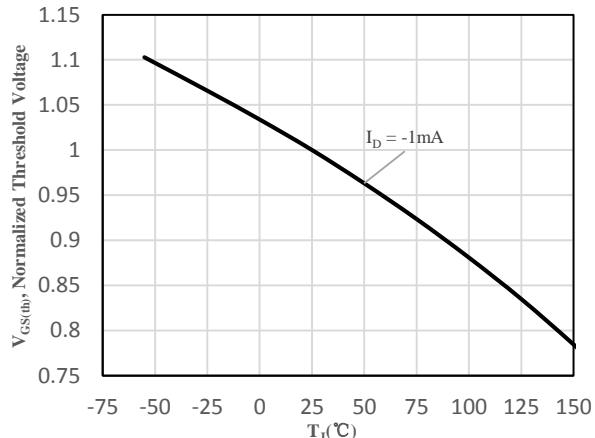
**Fig 4 Body-Diode Characteristics**



**Fig 5 Normalized On-Resistance vs. Junction Temperature**



**Fig 6 Transfer Characteristics**


**Fig 7 Capacitance Characteristics**

**Fig 8 Gate-Charge Characteristics**

**Fig 9 Normalized Breakdown Voltage  
vs. Junction Temperature**

**Fig 10 Normalized  $V_{GS(th)}$  vs. Junction Temperature**



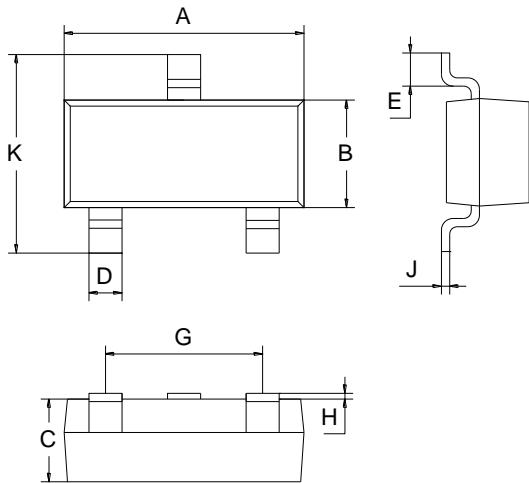
**BSS84/BSS84-3L/BSS84W**

P-Channel Enhancement Mode MOSFET



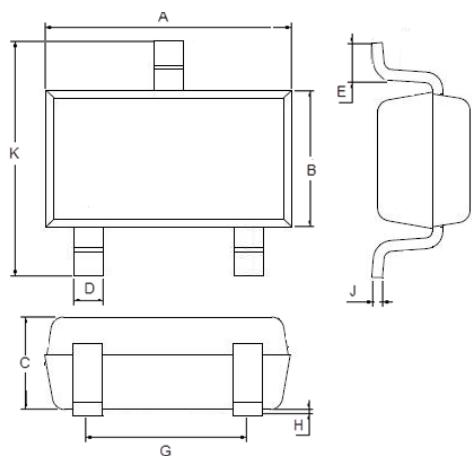
## Package Outline Dimensions (Unit: mm)

### SOT-23



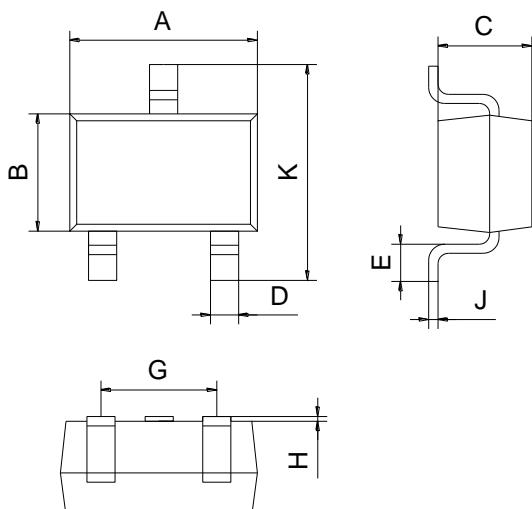
SOT-23		
Dimension	Min.	Max.
A	2.70	3.10
B	1.10	1.50
C	0.90	1.10
D	0.30	0.50
E	0.35	0.48
G	1.80	2.00
H	0.02	0.10
J	0.05	0.15
K	2.20	2.60

### SOT-23-3L



SOT-23-3L		
Dimension	Min.	Max.
A	2.80	3.00
B	1.50	1.70
C	1.00	1.20
D	0.35	0.45
E	0.35	0.55
G	1.80	2.00
H	0.02	0.10
J	0.10	0.20
K	2.60	3.00

### SOT-323



SOT-323		
Dimension	Min.	Max.
A	2.00	2.20
B	1.15	1.35
C	0.90	1.10
D	0.15	0.35
E	0.25	0.40
G	1.20	1.40
H	0.02	0.10
J	0.05	0.15
K	2.20	2.40



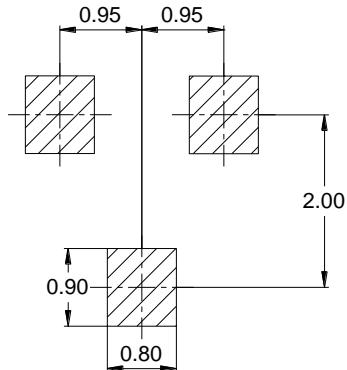
BSS84/BSS84-3L/BSS84W

P-Channel Enhancement Mode MOSFET

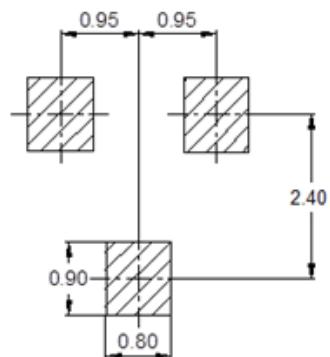


## Mounting Pad Layout (Unit: mm)

### SOT-23



### SOT-23-3L



### SOT-323

